

**N-CHANNEL 60V - 0.1  $\Omega$  - 2A TO-92**  
**STripFET™ II POWER MOSFET**

TYPE	V <sub>DSS</sub>	R <sub>D(on)</sub>	I <sub>D</sub>
STQ2NF06L	60 V	<0.12 $\Omega$	2 A

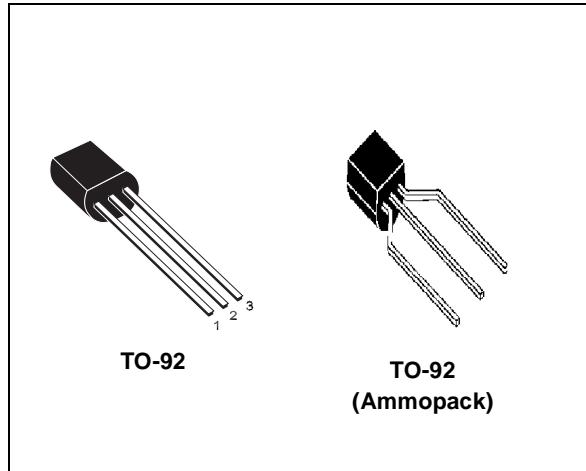
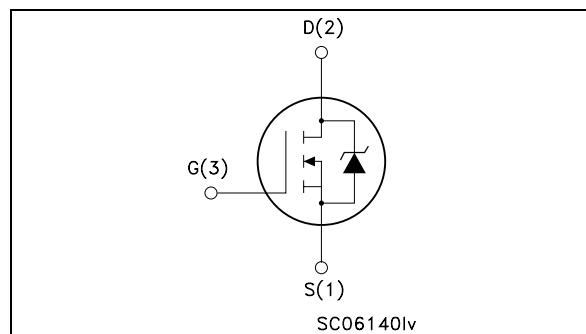
- TYPICAL R<sub>D(on)</sub> = 0.1  $\Omega$
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- AVALANCHE RUGGED TECHNOLOGY
- LOW THRESHOLD DRIVE

**DESCRIPTION**

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

**APPLICATIONS**

- DC MOTOR CONTROL (DISK DRIVES, etc.)
- DC-DC & DC-AC CONVERTERS
- SYNCHRONOUS RECTIFICATION


**INTERNAL SCHEMATIC DIAGRAM**

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 k $\Omega$ )	60	V
V <sub>GS</sub>	Gate- source Voltage	$\pm 16$	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	2	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	1.2	A
I <sub>DM(•)</sub>	Drain Current (pulsed)	8	A
P <sub>tot(1)</sub>	Total Dissipation at T <sub>C</sub> = 25°C	3	W
	Derating Factor	8	W/°C
dv/dt (2)	Peak Diode Recovery voltage slope	6	V/ns
E <sub>AS</sub> (3)	Single Pulse Avalanche Energy	200	mJ
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature		°C

(•) Pulse width limited by safe operating area.

(1) Related to R<sub>thj</sub> -

(2) I<sub>D</sub> ≤ 2A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

(3) Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 2A, V<sub>DD</sub> = 30V

## STQ2NF06L

### THERMAL DATA

Rthj-lead Rthj-amb T <sub>l</sub>	Thermal Resistance Junction-Lead Thermal Resistance Junction-ambient Maximum Lead Temperature For Soldering Purpose	Max Max Typ	40 125 260	°C/W °C/W °C
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### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

#### OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 µA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	µA µA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 16 V			±100	nA

#### ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 µA	1			V
R <sub>D(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 1 A V <sub>GS</sub> = 5 V I <sub>D</sub> = 1 A		0.1 0.12	0.12 0.14	Ω Ω

#### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 15 V I <sub>D</sub> = 1 A		3		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25V f = 1 MHz V <sub>GS</sub> = 0		360 55 25		pF pF pF

## ELECTRICAL CHARACTERISTICS (continued)

## SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Time Rise Time	$V_{DD} = 30 \text{ V}$ $I_D = 1 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 4.5 \text{ V}$ (Resistive Load, Figure 3)		10 20		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48 \text{ V}$ $I_D = 2 \text{ A}$ $V_{GS} = 5 \text{ V}$		5.6 1.2 2.6	7.6	nC nC nC

## SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 30 \text{ V}$ $I_D = 1 \text{ A}$ $R_G = 4.7 \Omega$ , $V_{GS} = 4.5 \text{ V}$ (Resistive Load, Figure 3)		17 6		ns ns

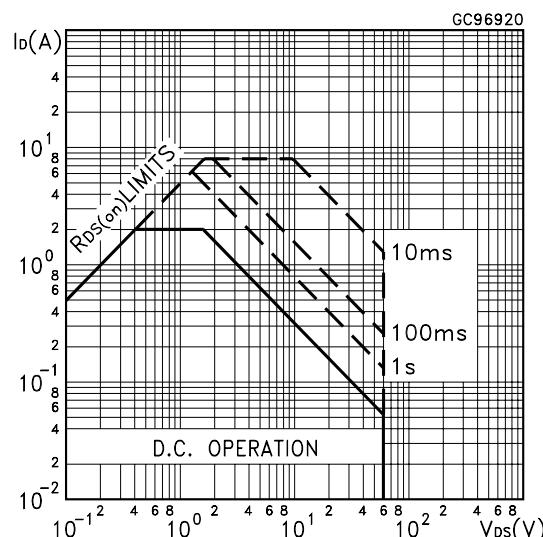
## SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				2 8	A A
$V_{SD} (\bullet)$	Forward On Voltage	$I_{SD} = 2 \text{ A}$ $V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 2 \text{ A}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 20 \text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		28 31 2.2		ns nC A

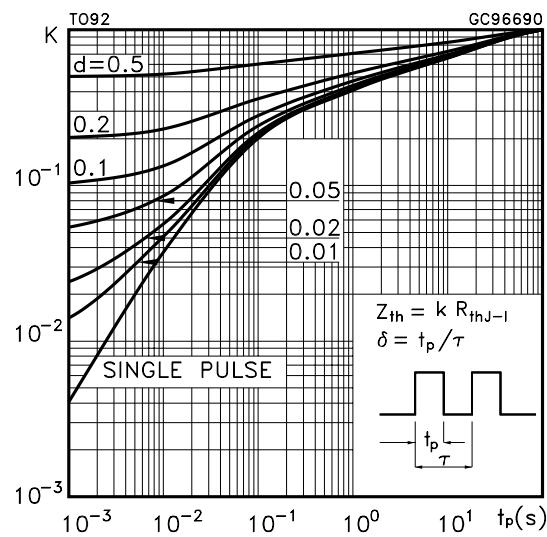
(\*)Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

(\bullet)Pulse width limited by safe operating area.

## Safe Operating Area

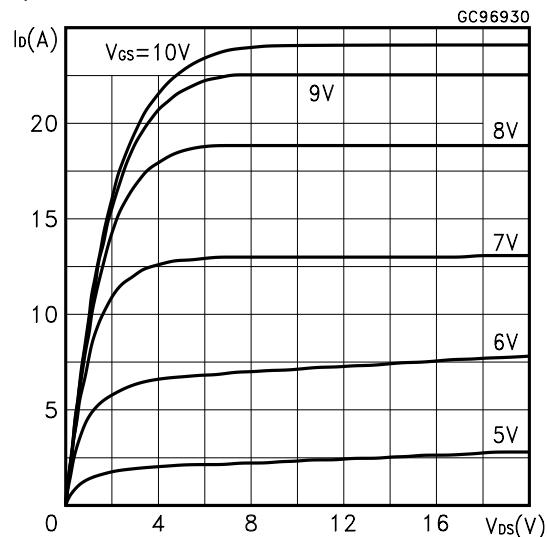


## Thermal Impedance Junction-lead

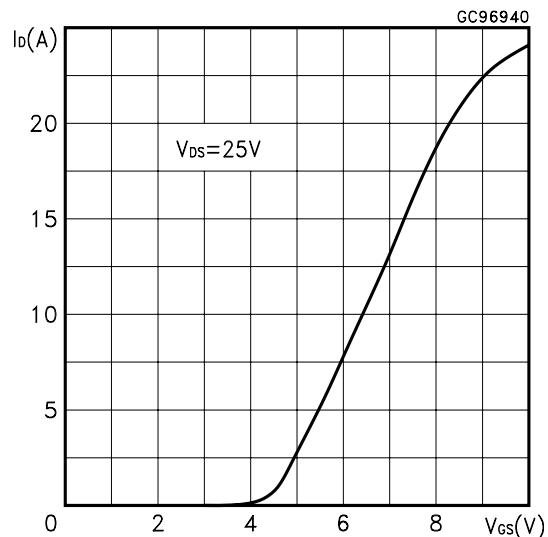


# STQ2NF06L

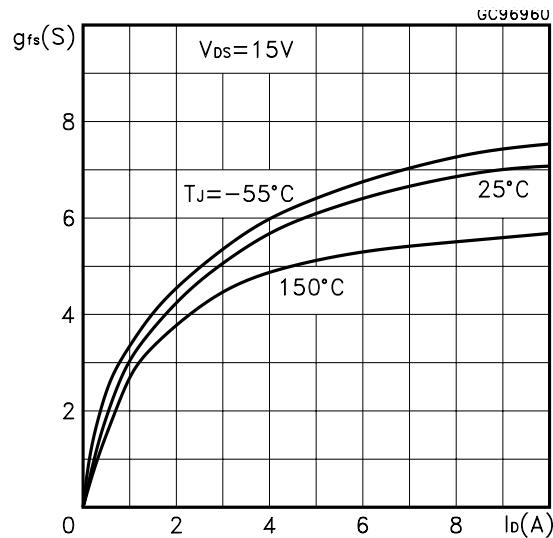
Output Characteristics



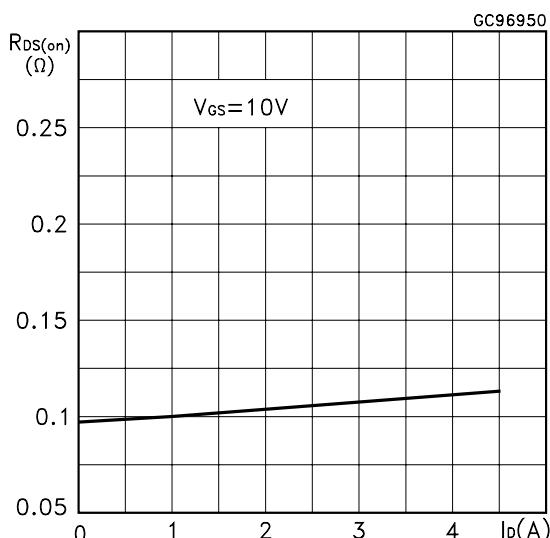
Transfer Characteristics



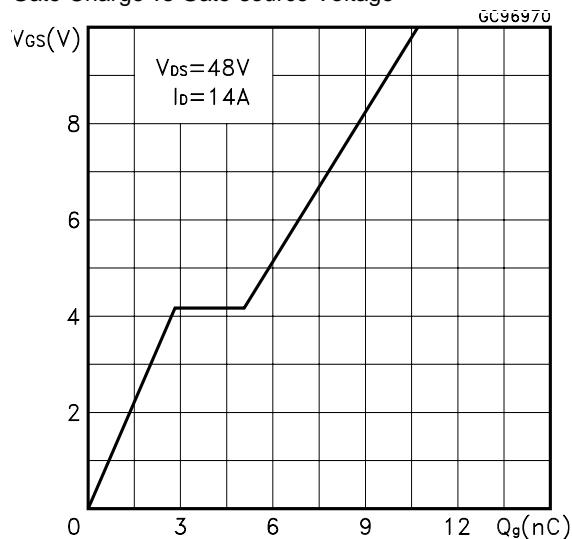
Transconductance



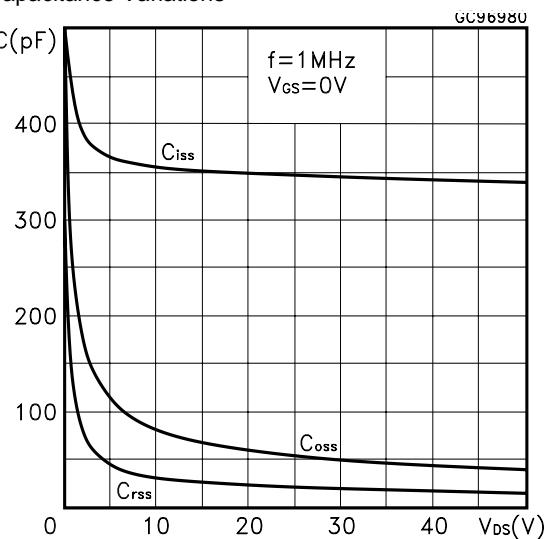
Static Drain-source On Resistance



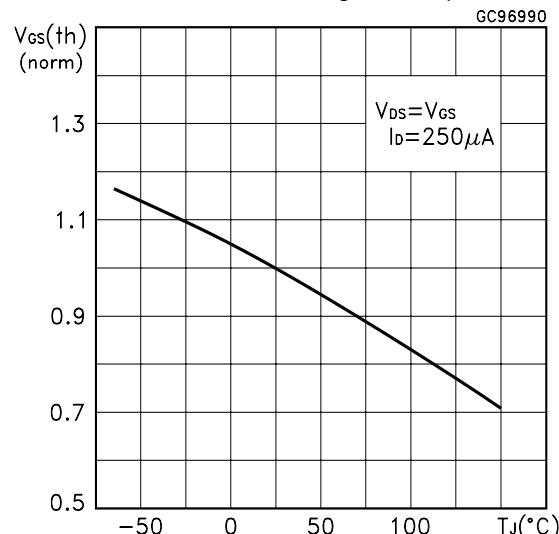
Gate Charge vs Gate-source Voltage



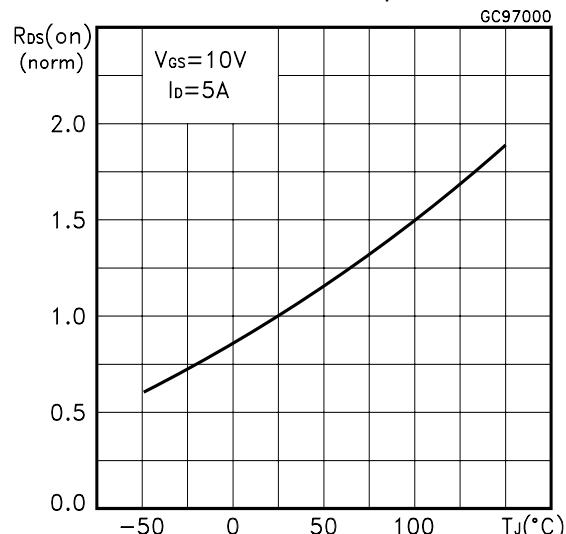
Capacitance Variations



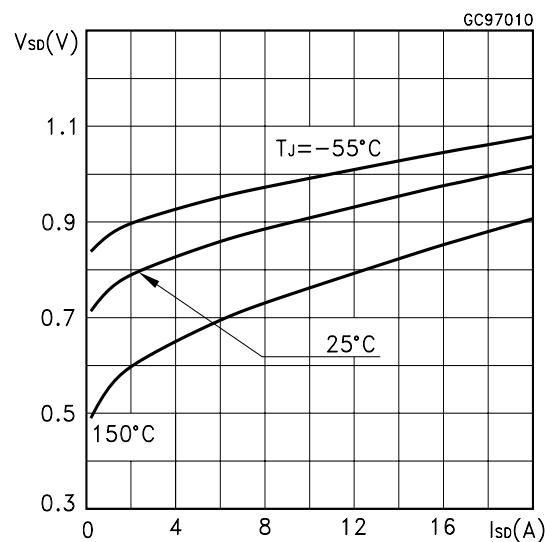
Normalized Gate Threshold Voltage vs Temperature



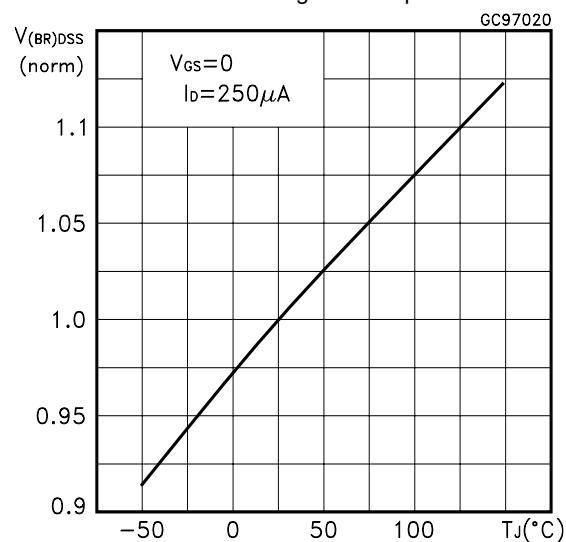
Normalized on Resistance vs Temperature



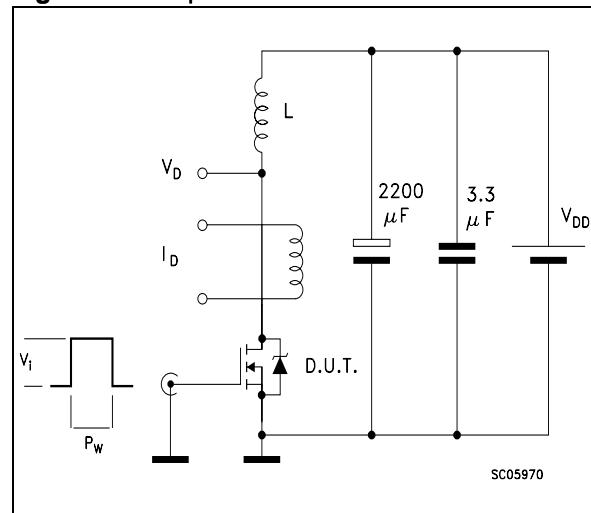
Source-drain Diode Forward Characteristics



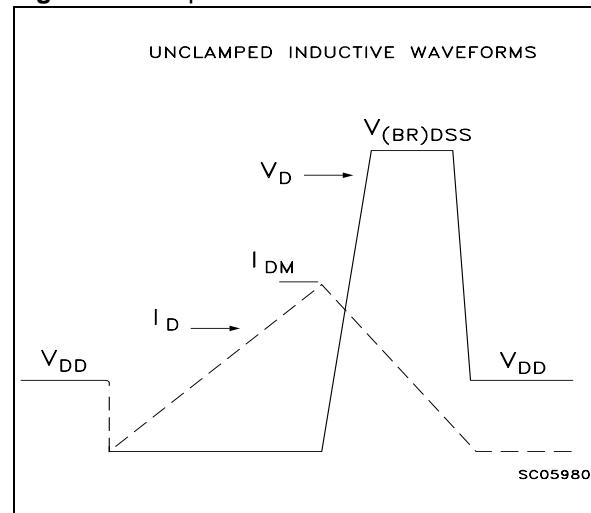
Normalized Breakdown Voltage vs Temperature.



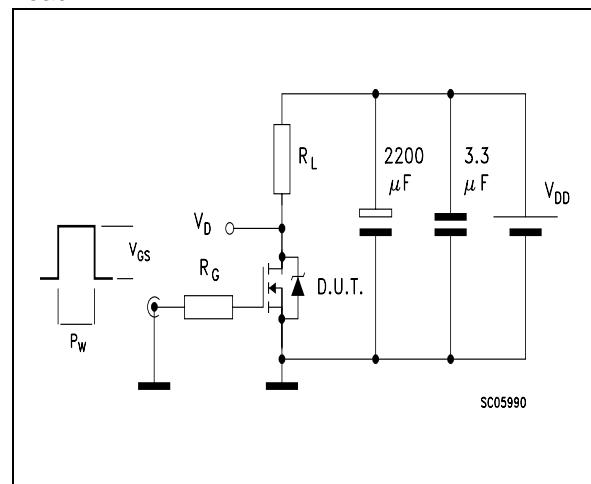
**Fig. 1: Unclamped Inductive Load Test Circuit**



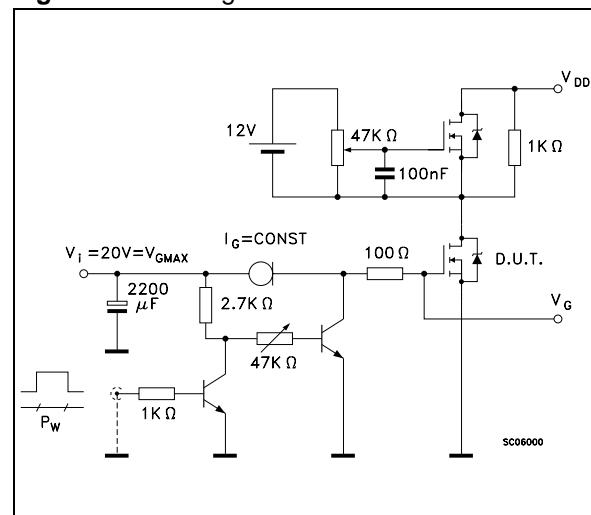
**Fig. 2: Unclamped Inductive Waveform**



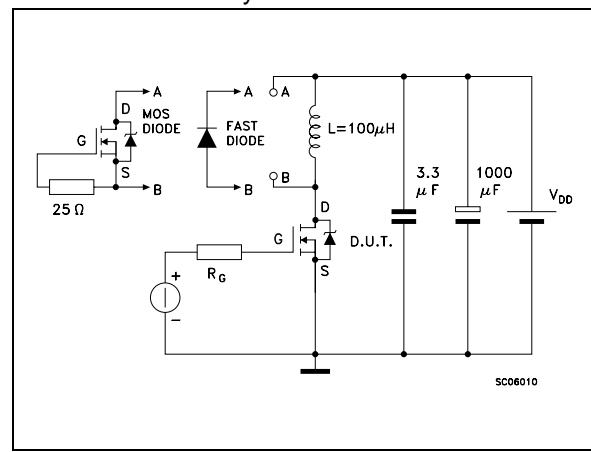
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

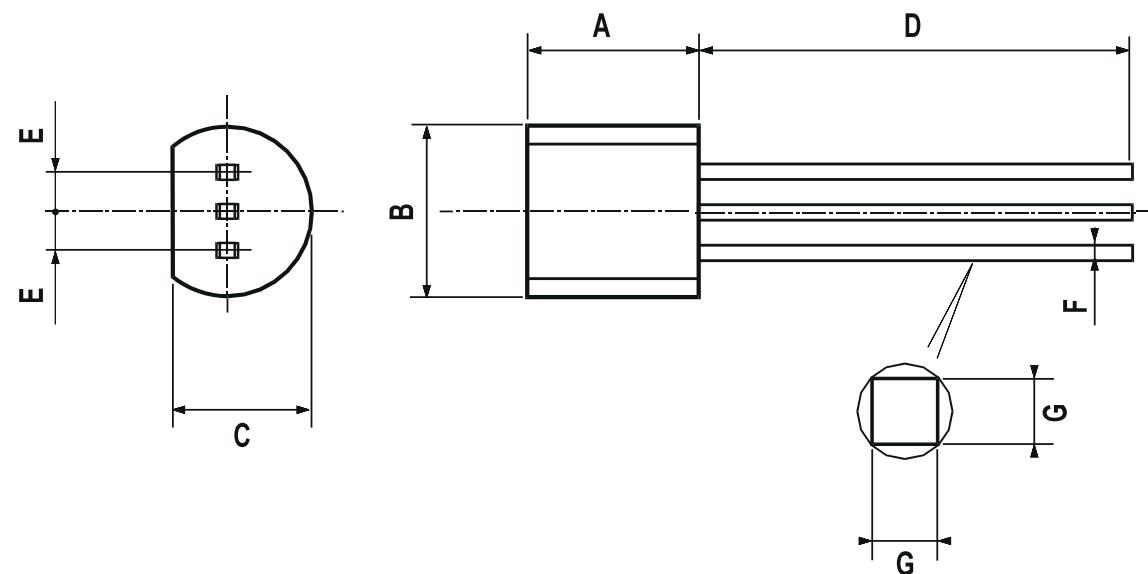


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



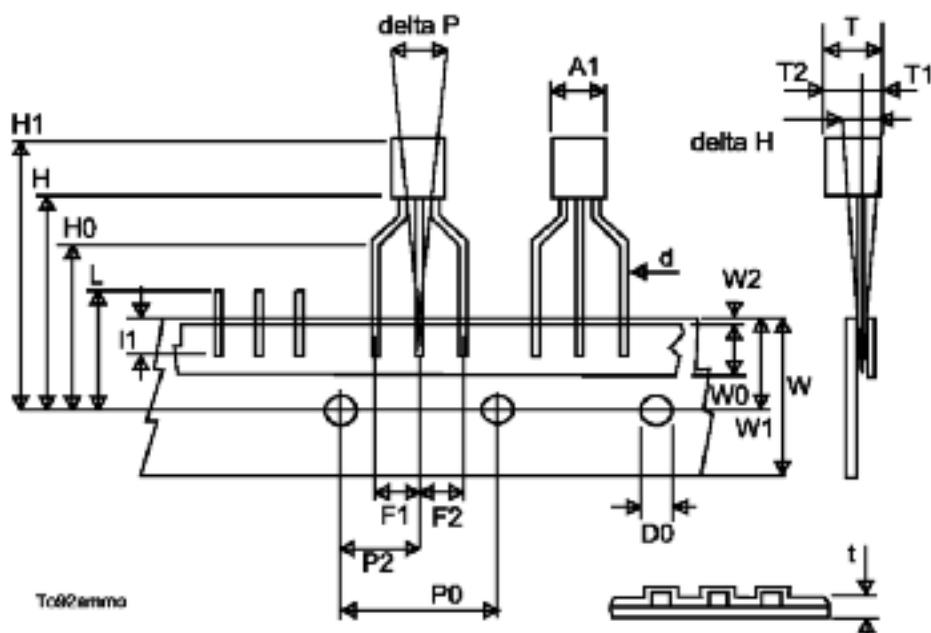
## TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.58		5.33	0.180		0.210
B	4.45		5.2	0.175		0.204
C	3.2		4.2	0.126		0.165
D	12.7			0.500		
E		1.27			0.050	
F	0.4		0.51	0.016		0.020
G	0.35			0.14		



## TO-92 AMMOPACK

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A1			4.8			0.19
T			3.8			0.15
T1			1.6			0.06
T2			2.3			0.09
d			0.48			0.02
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
I1	3			0.11		
delta P	-1		1	-0.04		0.04



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